

IN THE CLAIMS

Please amend claims 1-6, and claim 8 as follows:

1(Amended). A method of forming a CMOS sidewall spacer, comprising the steps of:

forming a PMOS transistor gate structure on a n-type region of a semiconductor substrate;

forming a NMOS transistor gate structure on a p-type region of said semiconductor substrate;

forming single layer sidewall structures adjacent to said NMOS transistor gate structure and said PMOS transistor gate structure; and

etching said single layer sidewall structure adjacent to said NMOS transistor gate structure such that the width of the single layer sidewall structure adjacent to said NMOS transistor gate structure is less than the width of the single layer sidewall structure adjacent to said PMOS transistor gate structure.

2(Amended). The method of claim 1 wherein said etching of said single layer sidewall structure is an anisotropic etch.

3(Amended). The method of claim 1 wherein said single layer sidewall structure is a material selected from the group consisting of silicon nitride, silicon oxide, and silicon oxynitride.

4(Amended). A method for forming CMOS sidewall spacers, comprising the steps of:

providing a semiconductor substrate of a first conductivity type with a region of a second conductivity type;

forming a gate dielectric on said semiconductor substrate;

forming a conductive layer on said gate dielectric;

etching said conductive layer and said gate dielectric to form a first transistor gate stack with an upper surface on said semiconductor substrate of a first conductivity and a second transistor gate stack with an upper surface on said region of said semiconductor substrate of a second conductivity type;

forming at least one first single layer sidewall structure of a first width adjacent to said second transistor gate stack; and

forming at least one second single layer sidewall structure of a second width adjacent to said first transistor gate stack wherein said second width is less than said first width.

5(Amended). The method of claim 4 where said forming at least one first single layer sidewall structure of a first width comprises:

forming a single layer sidewall film over said semiconductor substrate; and

etching said single layer sidewall film using an anisotropic etch such that all of said single layer sidewall film is removed from said upper surface of said first transistor gate stack and a portion of said single layer sidewall film is left adjacent to said second transistor gate stack.

6(Amended). The method of claim 5 where the single layer sidewall film is silicon nitride, silicon oxide, or silicon oxynitride.

8(Amended). The method of claim 4 where said forming at least one second single layer sidewall structure of a second width comprises:

*A2* providing a first transistor gate stack with at least one adjacent single layer sidewall film of a first width;

masking said second transistor gate stack using a source drain implant mask; and

etching said single layer sidewall film of a first width adjacent to said first transistor gate stack.